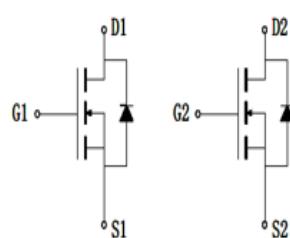
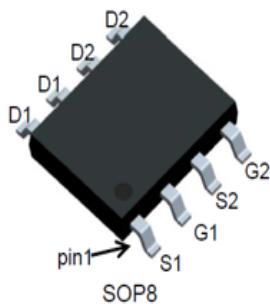




N-Channel Enhancement Mode Field Effect Transistor



Product Summary

- V_{DS} 60V
- I_D 5.0A
- $R_{DS(ON)}$ (at $V_{GS} = 10V$) <44mohm
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) <49mohm

General Description

- Trench Power MV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching

SOP-8

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | | Symbol | Maximum | Unit |
|--|---------------------------------------|-----------------|----------|---------------------------|
| Drain-source Voltage | | V_{DS} | 60 | V |
| Gate-source Voltage | | V_{GS} | ± 20 | V |
| Drain Current | $T_A=25^\circ\text{C}$ @ Steady State | I_D | 5.0 | A |
| | $T_A=70^\circ\text{C}$ @ Steady State | | 4.0 | |
| Pulsed Drain Current ^A | | I_{DM} | 25 | A |
| Total Power Dissipation @ $T_A=25^\circ\text{C}$ | | P_D | 3.1 | W |
| Thermal Resistance Junction-to-Ambient @ Steady State ^B | | $R_{\theta JA}$ | 40.3 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | | T_J, T_{STG} | -55~+150 | $^\circ\text{C}$ |

■ Ordering Information (Example)

| PREFERRED P/N | PACKING CODE | Marking | MINIMUM PACKAGE(pcs) | INNER BOX QUANTITY(pcs) | OUTER CARTON QUANTITY(pcs) | DELIVERY MODE |
|---------------|--------------|---------|----------------------|-------------------------|----------------------------|---------------|
| YJS05N06A | F2 | Q05N06 | 4000 | 8000 | 64000 | 13" reel |



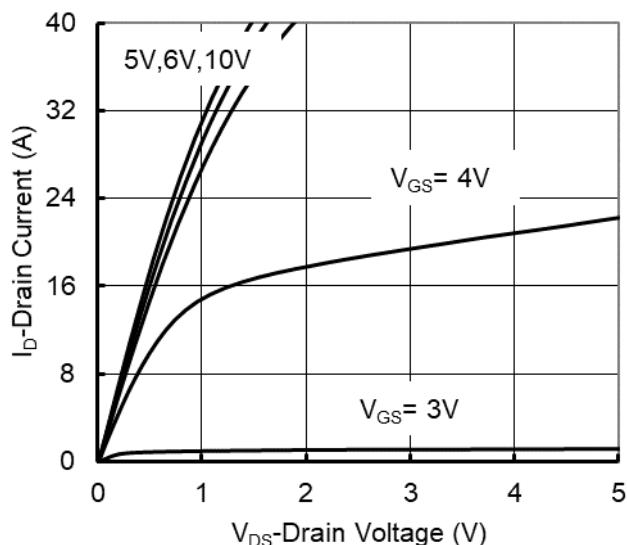
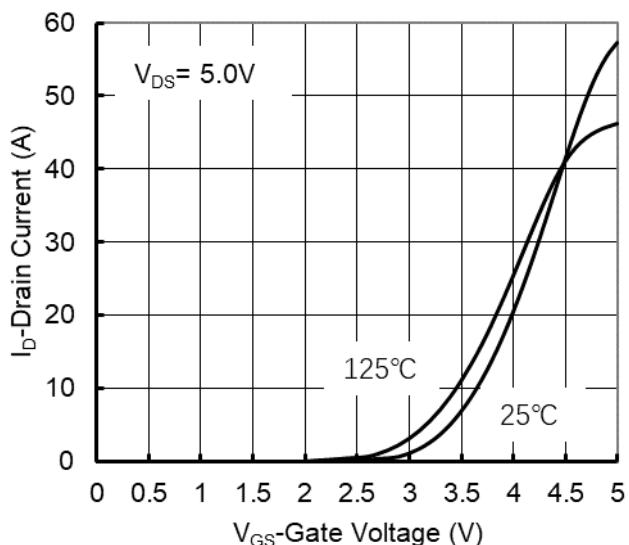
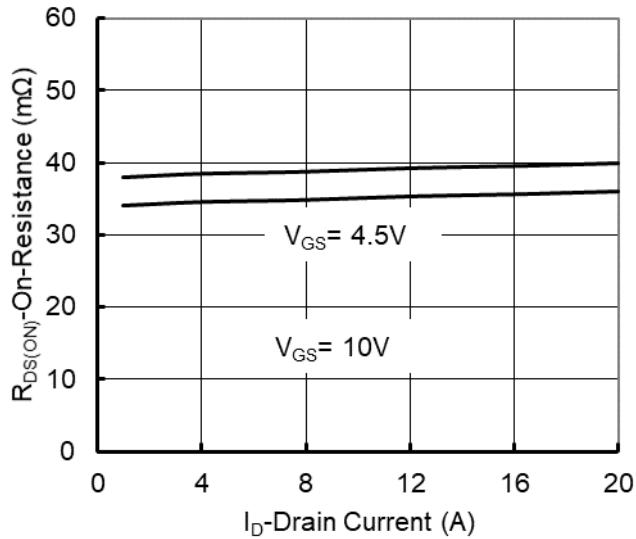
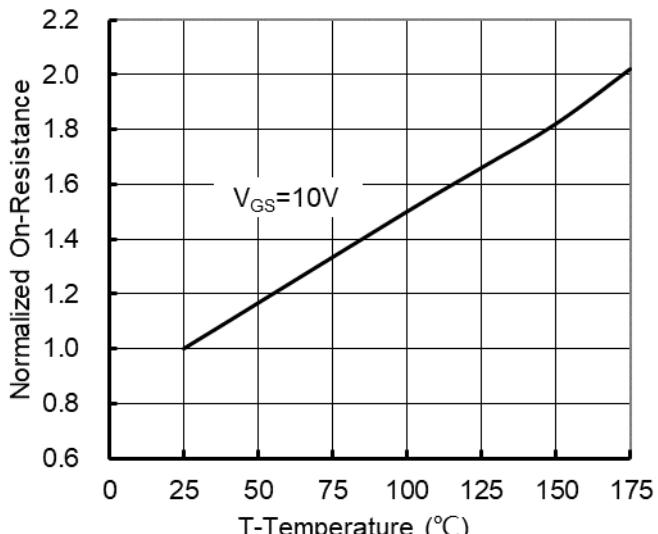
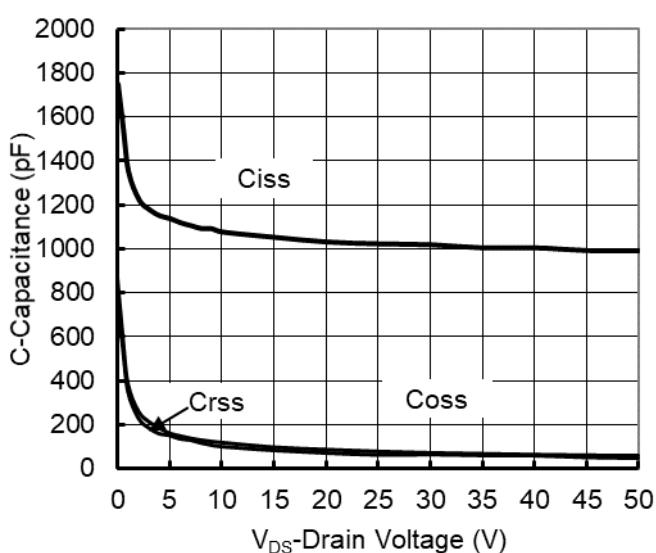
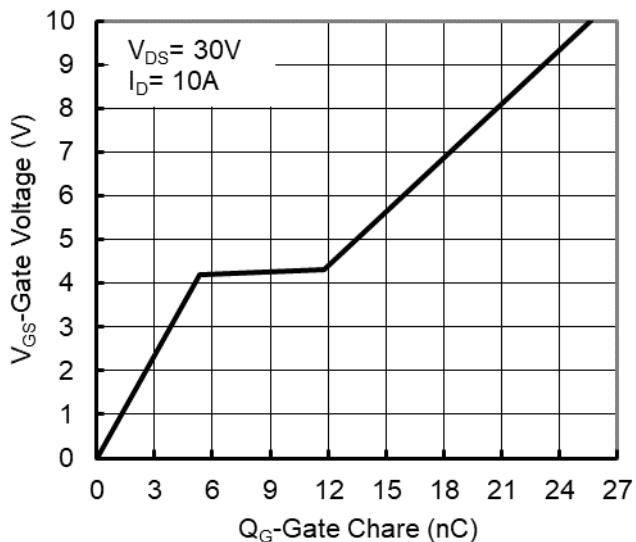
YJS05N06A

■ Electrical Characteristics ($T_J=25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Conditions | Min | Typ | Max | Units |
|---------------------------------------|--------------|--|-----|------|-----------|-----------|
| Static Parameter | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 60 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=60V, V_{GS}=0V$ | | | 1 | μA |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | | | ± 100 | nA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 1.0 | 1.5 | 2.5 | V |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=5.0A$ | | 35 | 44 | $m\Omega$ |
| | | $V_{GS}=4.5V, I_D=4.0A$ | | 39 | 49 | |
| Diode Forward Voltage | V_{SD} | $I_S=5.0A, V_{GS}=0V$ | | 0.8 | 1.2 | V |
| Maximum Body-Diode Continuous Current | I_S | | | | 5.0 | A |
| Dynamic Parameters | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=30V, V_{GS}=0V, f=1MHz$ | | 1018 | | pF |
| Output Capacitance | C_{oss} | | | 70 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 62 | | |
| Switching Parameters | | | | | | |
| Total Gate Charge | Q_g | $V_{GS}=10V, V_{DS}=30V, I_D=10A$ | | 26 | | nC |
| Gate Source Charge | Q_{gs} | | | 5.4 | | |
| Gate Drain Charge | Q_{gd} | | | 6.5 | | |
| Reverse Recovery Charge | Q_{rr} | $I_F=20A, dI/dt=500A/us$ | | 11.7 | | ns |
| Reverse Recovery Time | t_{rr} | | | 23 | | |
| Turn-on Delay Time | $t_{D(on)}$ | | | 10 | | |
| Turn-on Rise Time | t_r | $V_{GS}=10V, V_{DD}=30V, I_D=2A, R_L=1\Omega, R_{GEN}=3\Omega$ | | 20 | | |
| Turn-off Delay Time | $t_{D(off)}$ | | | 29 | | |
| Turn-off Fall Time | t_f | | | 21 | | |

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-lead and lead-to-ambient thermal resistance, where the lead thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JL}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.

**■ Typical Performance Characteristics****Figure 1. Output Characteristics****Figure 2. Transfer Characteristics****Figure 3. On-Resistance vs. Drain Current and Gate Voltage****Figure 4. On-Resistance vs. Junction Temperature****Figure 5. Capacitance Characteristics****Figure 6. Gate Charge**

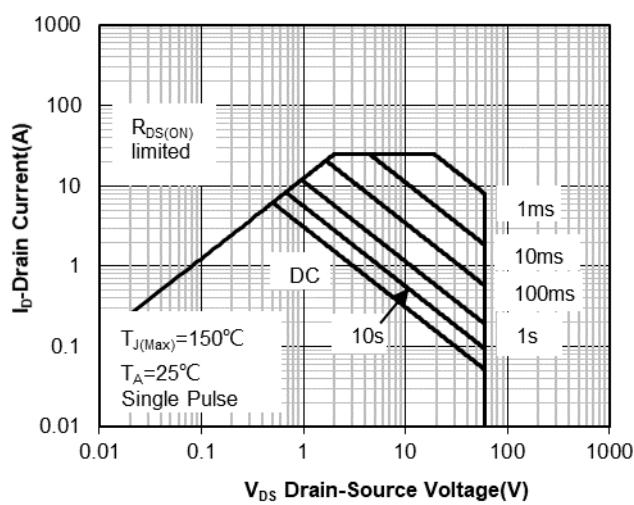


Figure 7. Safe Operation Area

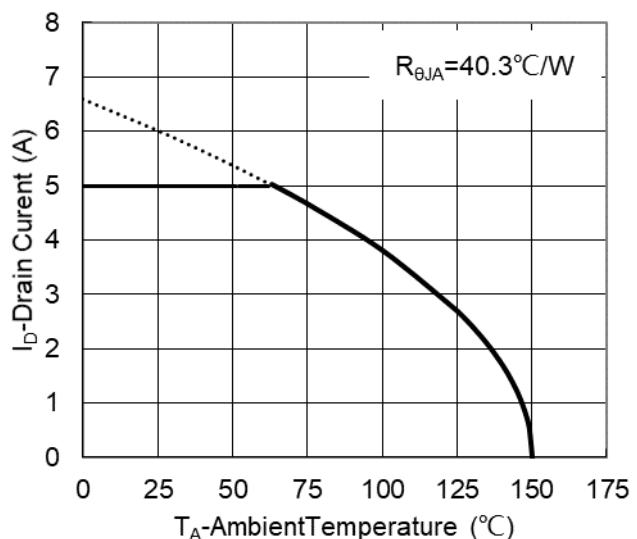


Figure 8. Maximum Continuous Drain Current vs Ambient Temperature

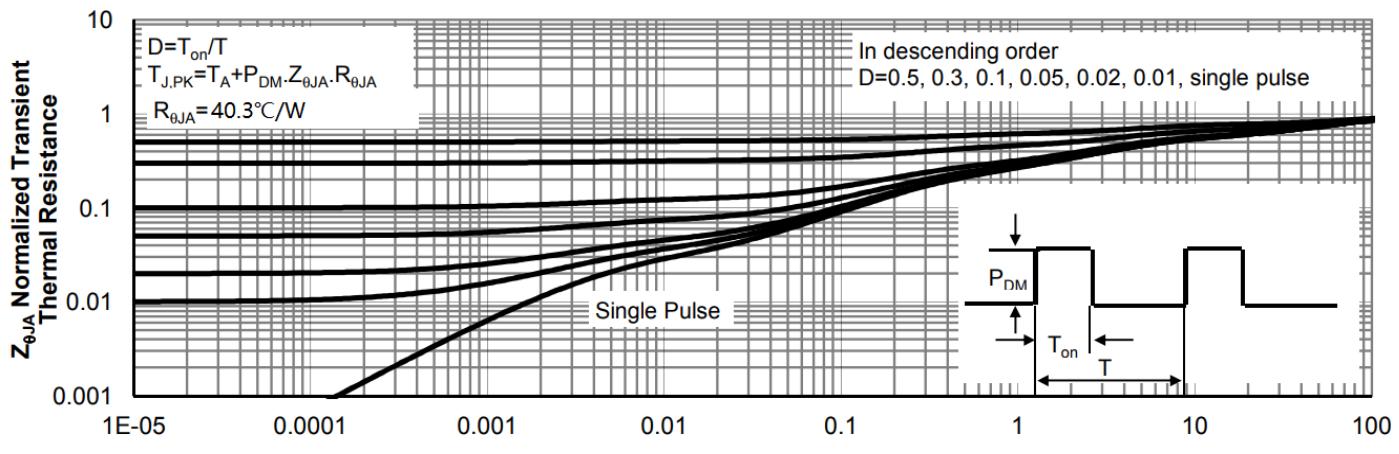
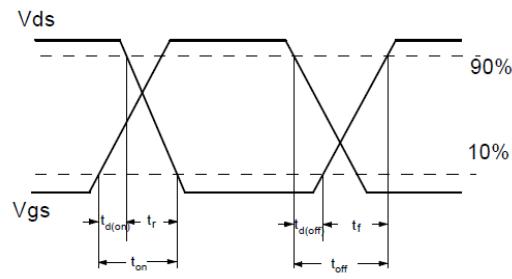
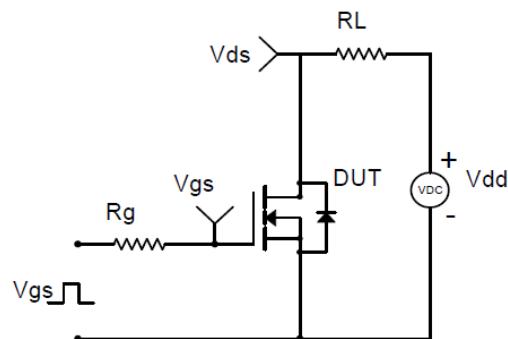
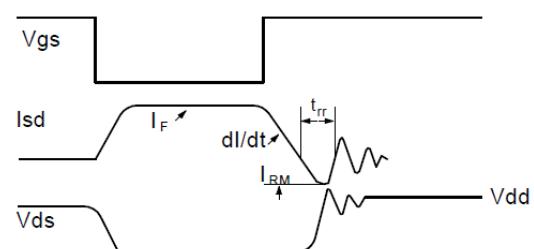
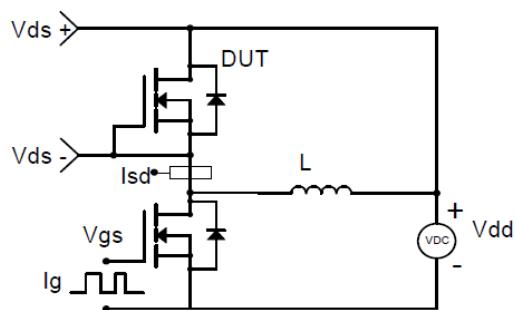


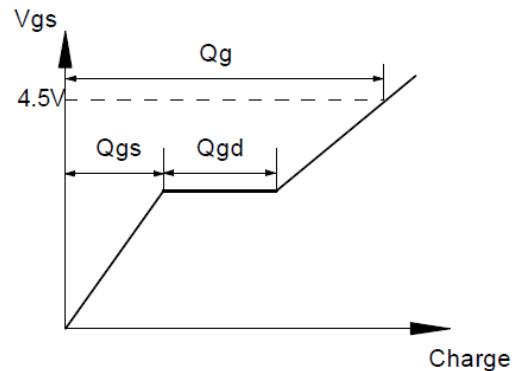
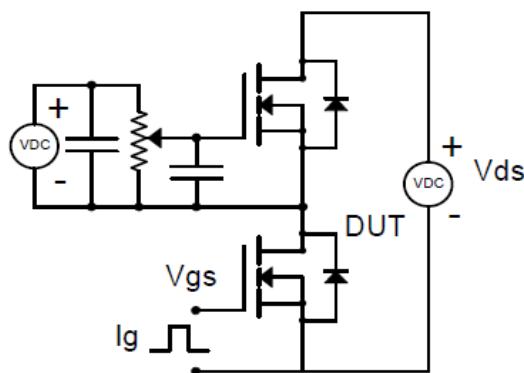
Figure 9. Normalized Maximum Transient Thermal Impedance



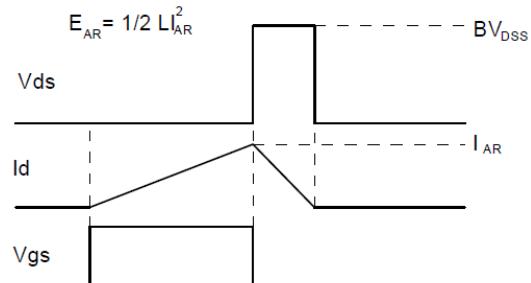
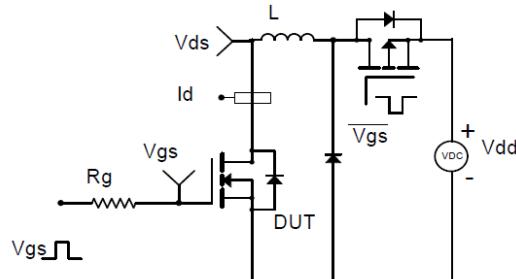
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



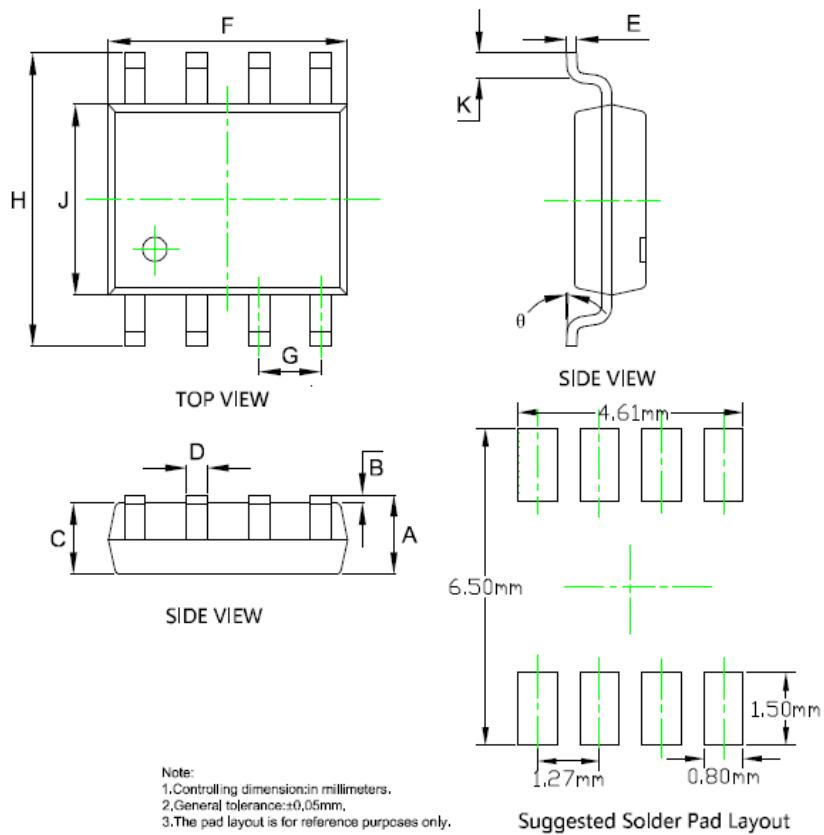
Gate Charge Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



■SOP-8 Package information



Note:
1. Controlling dimension in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

| SYMBOL | DIMENSIONS | | | |
|----------|------------|-------|------------|-------|
| | INCHES | | Millimeter | |
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.053 | 0.069 | 1.350 | 1.750 |
| B | 0.004 | 0.010 | 0.100 | 0.250 |
| C | 0.053 | 0.061 | 1.350 | 1.550 |
| D | 0.013 | 0.020 | 0.330 | 0.510 |
| E | 0.007 | 0.010 | 0.170 | 0.250 |
| F | 0.189 | 0.197 | 4.800 | 5.000 |
| G | 0.050BSC | | 1.270BSC | |
| H | 0.228 | 0.244 | 5.800 | 6.200 |
| J | 0.150 | 0.157 | 3.800 | 4.000 |
| K | 0.016 | 0.050 | 0.400 | 1.270 |
| θ | 0° | 8° | 0° | 8° |



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com>, or consult your nearest Yangjie's sales office for further assistance.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Yangjie manufacturer:

Other Similar products are found below :

[MCH3443-TL-E](#) [MCH6422-TL-E](#) [FDPF9N50NZ](#) [NTNS3A92PZT5G](#) [IRFD120](#) [JANTX2N5237](#) [2N7000](#) [2SK2464-TL-E](#) [AOD464](#) [2SJ277-DL-E](#) [2SK2267\(Q\)](#) [2SK2545\(Q,T\)](#) [405094E](#) [423220D](#) [MIC4420CM-TR](#) [VN1206L](#) [614234A](#) [715780A](#) [SSM6J414TU,LF\(T](#) [751625C](#) [IRS2092STRPBF-EL](#) [IPS70R2K0CEAKMA1](#) [BSF024N03LT3 G](#) [PSMN4R2-30MLD](#) [TK31J60W5,S1VQ\(O](#) [2SK2614\(TE16L1,Q\)](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE2384](#) [NTE2969](#) [NTE6400A](#) [DMC2700UDMQ-7](#) [DMN2080UCB4-7](#) [DMN61D9UWQ-13](#) [US6M2GTR](#) [DMN31D5UDJ-7](#) [SSM6P54TU,LF](#) [DMP22D4UFO-7B](#) [IPS60R3K4CEAKMA1](#) [DMN1006UCA6-7](#) [DMN16M9UCA6-7](#) [STF5N65M6](#) [IRF40H233XTMA1](#) [IPSA70R950CEAKMA1](#) [IPSA70R2K0CEAKMA1](#) [STU5N65M6](#) [C3M0021120D](#) [DMN6022SSD-13](#)